Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

Fairchild Semiconductor
FCH76N60NF

For any questions, you can email us directly:
sales@integrated-circuit.com

FAIRCHILD SEMICONDUCTOR®

November 2013

FCH76N60NF

N-Channel SupreMOS® FRFET® MOSFET

600 V, 72.8 A, 38 mΩ

Features

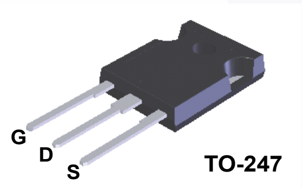
- $R_{DS(on)}$ = 28.7 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 38 A
- Ultra Low Gate Charge (Typ. Q_g = 230 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 896 pF)
- 100% Avalanche Tested
- RoHS Compliant

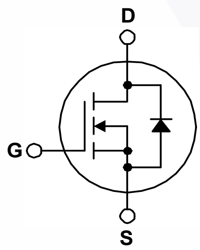
Application

- Solar Inverter
- AC-DC Power Supply

Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications. SupreMOS FRFET® MOSFET's optimized body diode reverse recovery performance can remove additional component and improve system reliability.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FCH76N60NF	Unit
V_{DSS}	Drain to Source Voltage		600	V
V_{GSS}	Gate to Source Voltage		±30	V
I_D	Drain Current	- Continuous (T_C = 25°C)	72.8	A
		- Continuous (T_C = 100°C)	46	
I_{DM}	Drain Current	- Pulsed (Note 1)	218	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		7381	mJ
I_{AR}	Avalanche Current (Note 1)		24.3	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		5.43	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		50	
P_D	Power Dissipation	(T_C = 25°C)	543	W
		- Derate above 25°C	4.34	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FCH76N60NF	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.23	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCH76N60NF	FCH76N60NF	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0 V, T_C = 25°C	600	-	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25°C	-	0.73	-	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 480 V, V_{GS} = 0 V	-	-	10	µA
		V_{DS} = 480 V, V_{GS} = 0 V, T_C = 125°C	-	-	100	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 µA	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 38 A	-	28.7	38.0	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 38 A	-	92	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 100 V, V_{GS} = 0 V f = 1 MHz	-	8305	11045	pF
C_{oss}	Output Capacitance		-	361	480	pF
C_{rss}	Reverse Transfer Capacitance		-	3.3	5.0	pF
C_{oss}	Output Capacitance	V_{DS} = 380 V, V_{GS} = 0V, f = 1 MHz	-	192	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 380 V, V_{GS} = 0 V	-	896	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DS} = 380 V, I_D = 38 A, V_{GS} = 10 V (Note 4)	-	230	300	nC
Q_{gs}	Gate to Source Gate Charge		-	44	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	95	-	nC
ESR	Equivalent Series Resistance(G-S)	f = 1 MHz	-	1.2	-	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 380 V, I_D = 38 A R_G = 4.7 Ω (Note 4)	-	51	112	ns
t_r	Turn-On Rise Time		-	44	98	ns
$t_{d(off)}$	Turn-Off Delay Time		-	213	436	ns
t_f	Turn-Off Fall Time		-	43	96	ns
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	76	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	228	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 38 A	-	-	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 38 A dI_F/dt = 100 A/µs	-	200	-	ns
Q_{rr}	Reverse Recovery Charge		-	1.8	-	µC

Notes:
1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 24.3 A, R_G = 25 Ω, starting T_J = 25°C.
3. $I_{SD} \leq$ 72.8 A, di/dt $\leq$ 1200 A/µs, $V_{DD} \leq$ 380 V, starting T_J = 25°C.
4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

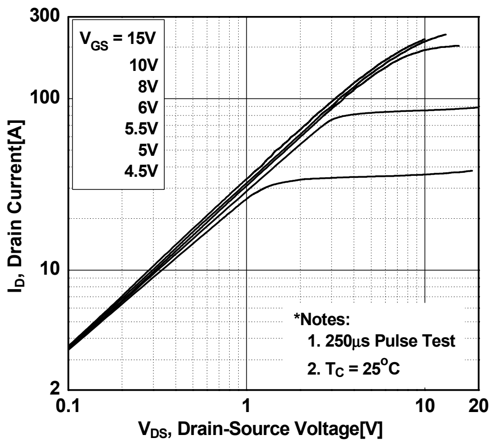


Figure 2. Transfer Characteristics

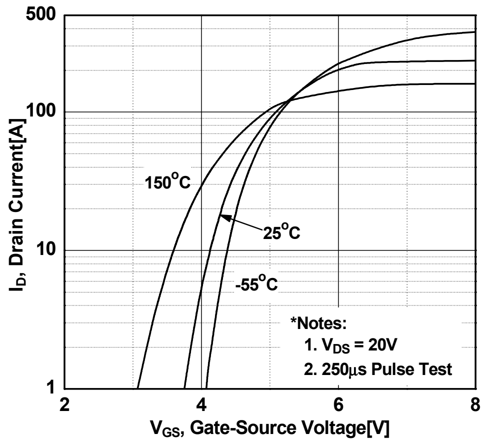


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

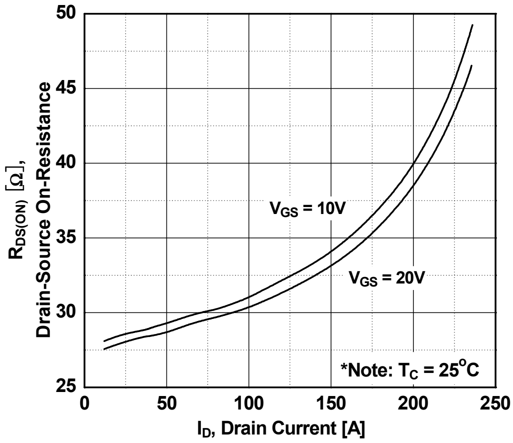


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

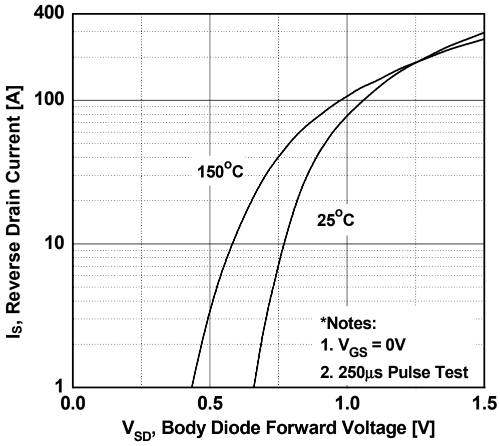


Figure 5. Capacitance Characteristics

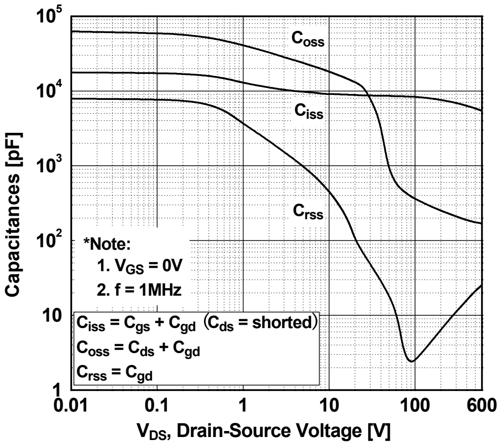
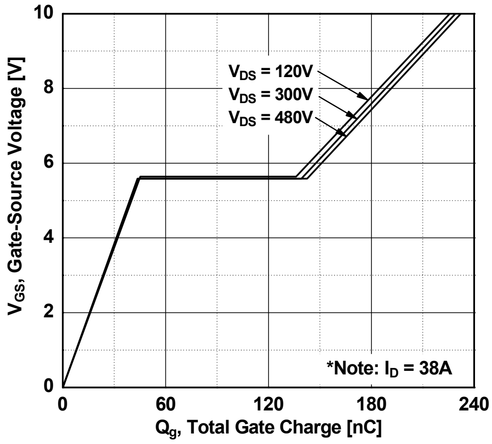


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

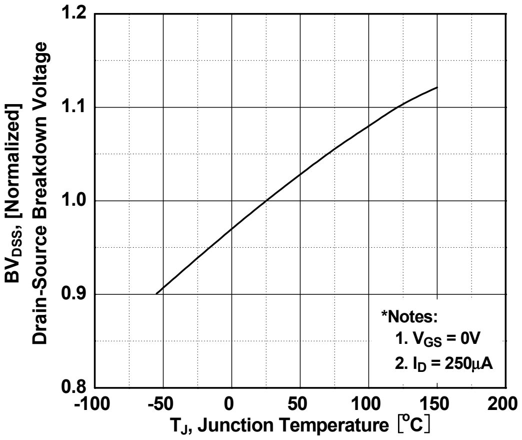


Figure 8. On-Resistance Variation vs. Temperature

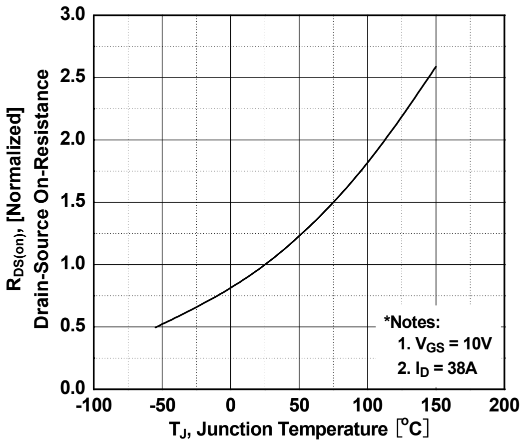


Figure 9. Maximum Safe Operating Area

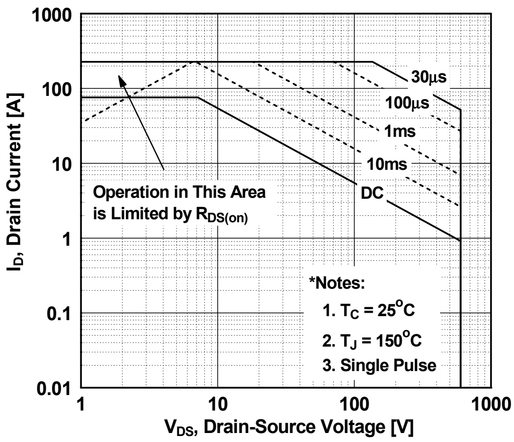


Figure 10. Maximum Drain Current vs. Case Temperature

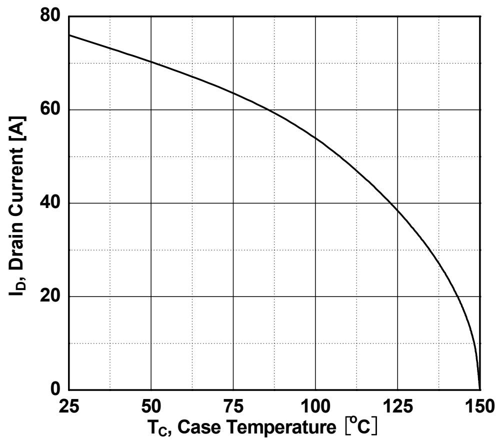
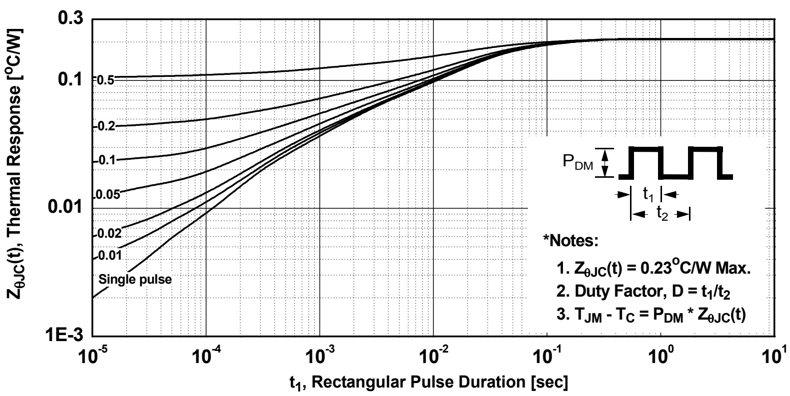


Figure 11. Transient Thermal Response Curve



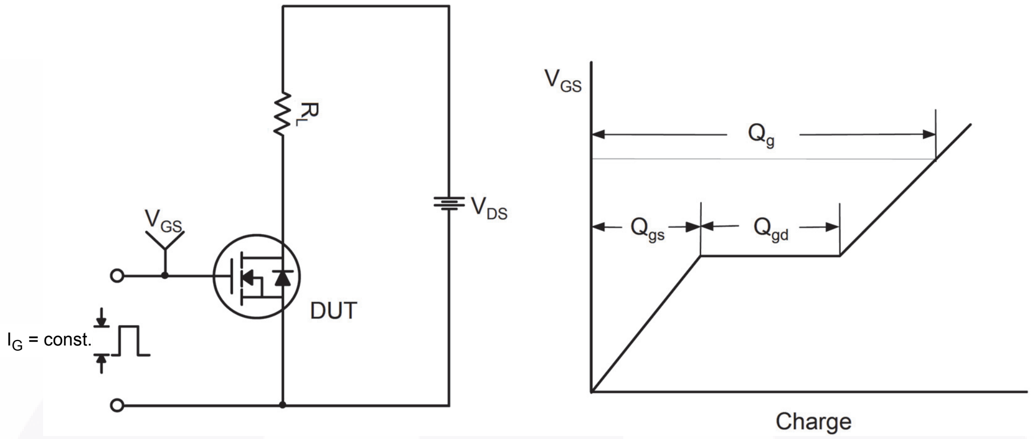


Figure 12. Gate Charge Test Circuit & Waveform

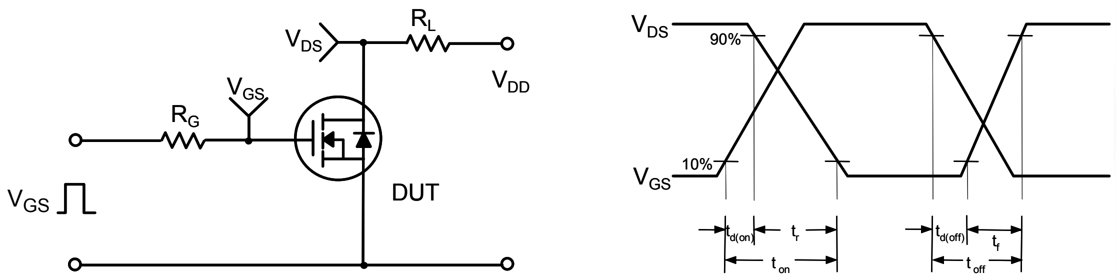


Figure 13. Resistive Switching Test Circuit & Waveforms

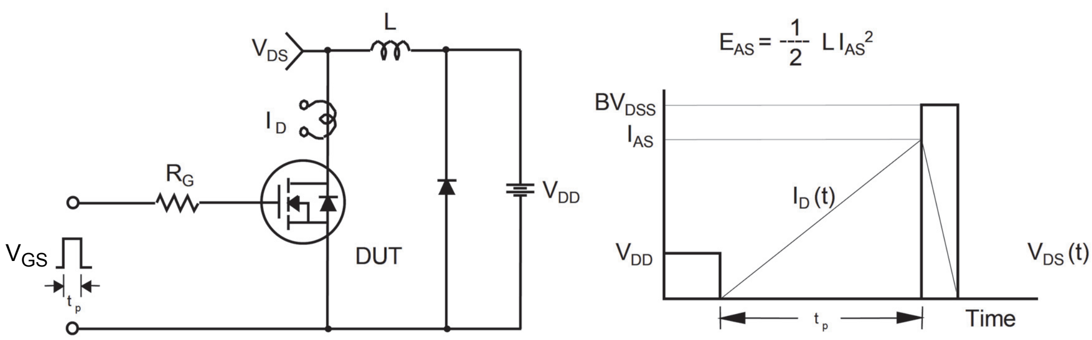


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

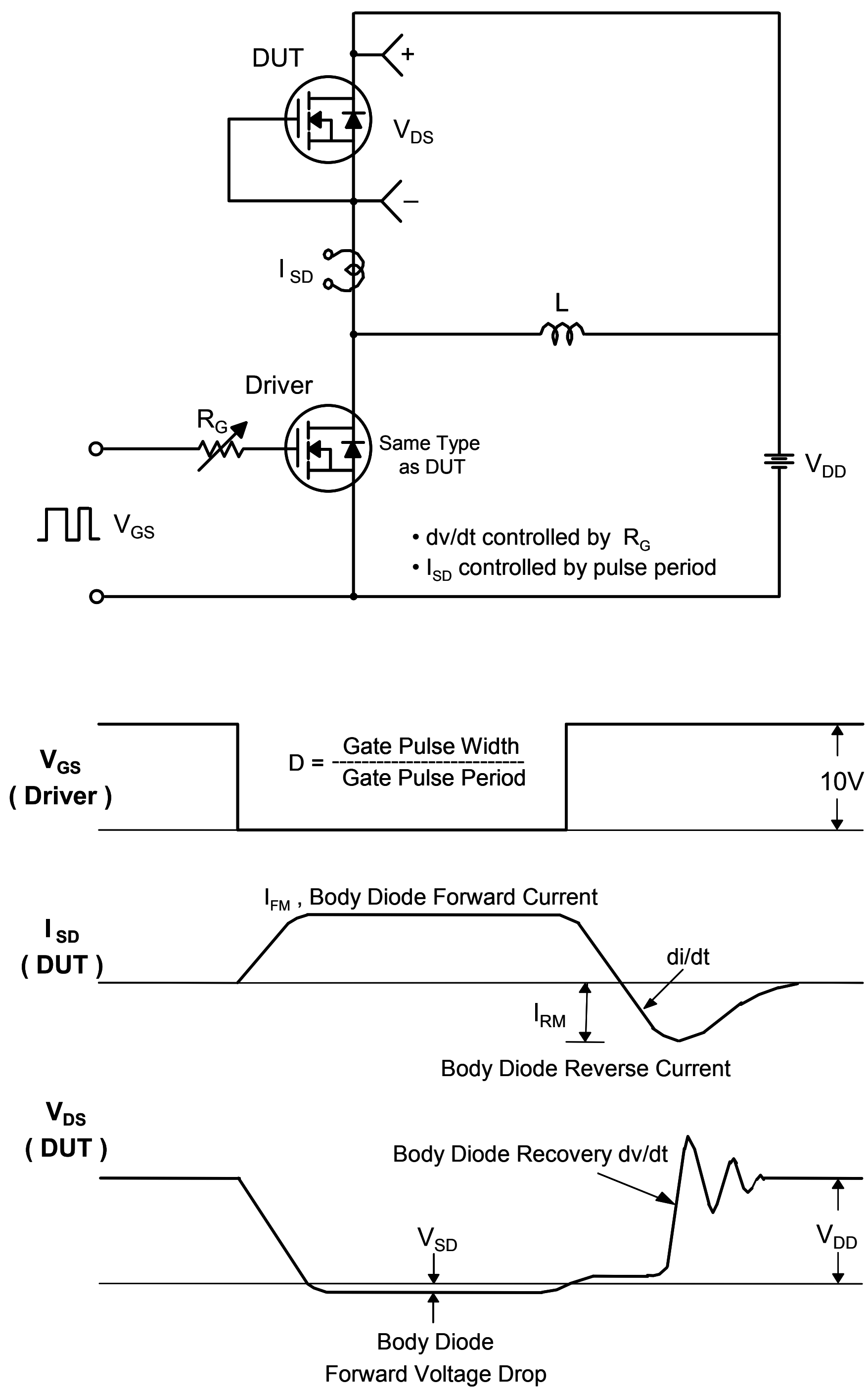
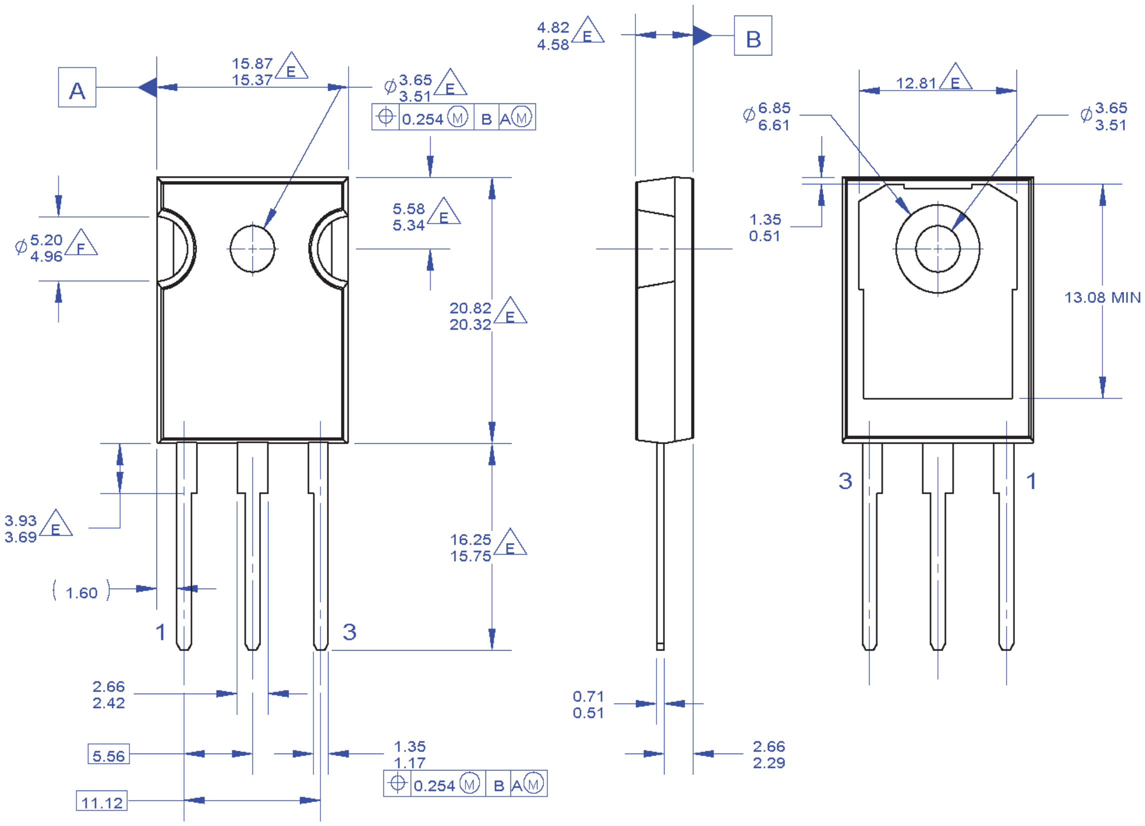


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
C. ALL DIMENSIONS ARE IN MILLIMETERS.
D. DRAWING CONFORMS TO ASME Y14.5 - 1994

E DOES NOT COMPLY JEDEC STANDARD VALUE

F NOTCH MAY BE SQUARE

G. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 16. TO-247, Molded, 3-Lead, Jedec Variation AB

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TO247-003

FAIRCHILD SEMICONDUCTOR®

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficentMax™
ESBC™
®
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™
F-PFS™
FRFET®
Global Power Resource^{SM}
GreenBridge™
Green FPS™
Green FPS™ e-Series™
Gmax™
GTO™
IntelliMAX™
ISOPLANAR™
Marking Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
mWSaver®
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
®
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™
SYSTEM GENERAL®*
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®*
µSerDes™
SerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS
Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I66